

5
10

A process for making semiconductor structures uses a decoupled plasma source to produce a highly selective plasma etchant to form a structure with a thin adhesive layer and overlaying conductive layer. The preferred plasma is formed from chlorine and oxygen feed gases. The highly conductive semiconductor structure has a thickness less than about 3000Å, preferably less than about 2600Å, and incorporates an adhesive layer that is preferably less than about 100Å thick. Despite the reduced profile and topography of the structure, it is more conductive than prior structures, and provides a robust device.